

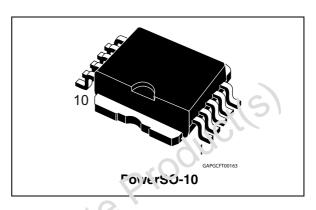
## **VB125ASPTR-E**

## High voltage ignition coil driver power integrated circuit

Туре	V <sub>cl</sub>	I <sub>cl</sub>	I <sub>CC</sub>
VB125ASPTR-E	340 V	11.1 A	200 mA

#### **Features**

- ECOPACK®: lead free and RoHS compliant
- Automotive Grade: compliance with AEC guidelines
- Primary coil voltage internally set
- Coil current limit internally set
- Logic level compatible input
- Battery operation
- Single flag-on coil current
- Temperature compensated high voltage clamp



### Description

The VB125ASPTR-E is a high voltage power integrated circuit made using the STMicroelectronics™ VIPower™ M1-2 technology, with vertical current flow power darlington and logic level compatible driving circuit.

The VB125ASPTR-E can be directly biased by using the 12 V battery voltage, thus avoiding to use a low voltage regulator. It has built-in protection circuit for coil current limiting and collector voltage clamping. It is suitable as smart, high voltage, high current interface in advanced electronic ignition system.

Table 1. Device summary

Package	Order code		
Раскаде	Tube	Tape and reel	
PowerSO-10		VB125ASPTR-E	

Contents VB125ASPTR-E

### **Contents**

1	Bloc	ck diagram and pins description	5
2	Elec	ctrical specifications	7
	2.1	Absolute maximum ratings	7
	2.2	Thermal data	7
	2.3	Electrical characteristics	8
3	Pacl	kage and packing information	<b>3</b> .  13
	3.1	ECOPACK®	13
	3.2	PowerSO-10 mechanical data	13
	3.3	PowerSO-10 packing information	15
005	Revi	Absolute maximum ratings Thermal data Electrical characteristics  kage and packing information  ECOPACK® PowerSO-10 mechanical data PowerSO-10 packing information  rision history	16

**577** 

VB125ASPTR-E List of tables

### List of tables

Table 1. Table 2. Table 3. Table 4. Table 5.	Device summary
Table 6. Table 7.	PowerSO-10 mechanical data
	aroduci(s)
	Obsolete
	Product(s)
Obsol	obsolete Producils).

**47**/

Doc ID 018829 Rev 1

3/17

List of figures VB125ASPTR-E

# **List of figures**

	Figure 1. Figure 2. Figure 3.	Block diagram
	Figure 4.	Electrical characteristic of the circuit shown in <i>Figure 3</i>
	Figure 6.	Output current waveform after thermal protection activation
	Figure 7. Figure 8.	Waveform
	Figure 9.	Application circuit
	Figure 10. Figure 11.	PowerSO-10 package dimensions
	Figure 12.	PowerSO-10 tube shipment (no suffix)
	i iguie 13.	Block diagram Configuration diagram (top view) Temperature compensated high voltage clamp Electrical characteristic of the circuit shown in Figure 3. 10 V <sub>cl</sub> with load L \( \geq 4 \text{ mH} \) . 10 Output current waveform after thermal protection activation
		ste Product(s)
C	)050''	

# 1 Block diagram and pins description

Figure 1. Block diagram

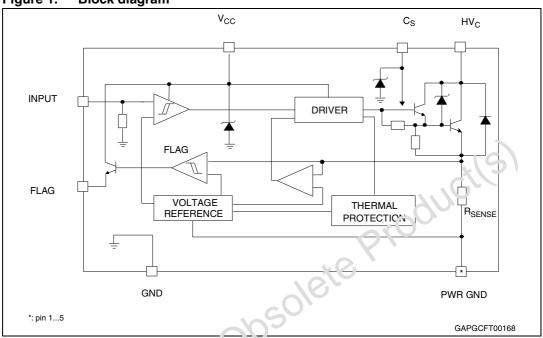


Figure 2. Configuration diagram (top view)

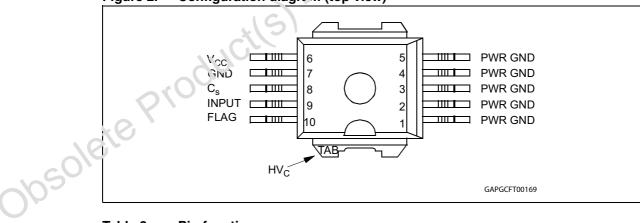


Table 2. Pin function

Pin number	Name	Function
1÷5	PWR GND	Emitter power ground
6	V <sub>CC</sub>	Logic supply voltage
7	GND	Control ground <sup>(1)</sup>
8	$C_s$	Logic level supply voltage filter capacitor
9	INPUT	Logic input channel

Table 2. Pin function (continued)

Pin number Name Function		Function
10	FLAG	Diagnostic output signal
TAB	HV <sub>C</sub>	Primary coil output signal

<sup>1.</sup> Pin 7 must be connected to pins 1,5 externally.

Obsolete Product(s). Obsolete Product(s)

## 2 Electrical specifications

#### 2.1 Absolute maximum ratings

Stressing the device above the rating listed in the *Table 3: Absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE program and other relevant quality documents.

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
HV <sub>c</sub>	Collector voltage (internally limited)	-0.3 to V <sub>3</sub>	V
I <sub>C</sub>	Collector current (internally limited)	(1),1	Α
V <sub>CC</sub>	Driving stage supply voltage	-0.2 to 40	٧
I <sub>CC</sub>	Driving circuit supply current	400	mA
I <sub>S</sub>	Logic circuit supply current	100	mA
V <sub>IN</sub>	Input voltage	-0.3 to 6	٧
P <sub>tot</sub>	Power dissipation at T <sub>C</sub> ≤ 25 °C	100	W
V <sub>ESD</sub>	ESD voltage (HV <sub>C</sub> pin)	-4 to 4	KV
V <sub>ESD</sub>	ESD voltage (other piri)	-2 to 2	KV
T <sub>j</sub>	Junction opera ing temperature	-40 to 150	°C
T <sub>stg</sub>	Storage tennierature range	-55 to 150	°C

#### 2.2 Thermal data

Tobie 4. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case (MAX)	1.2	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient (MAX)	62.5	°C/W

#### 2.3 Electrical characteristics

 $V_{CC}$  = 6 to 24 V; -40 °C <  $T_{j}$  < 125 °C;  $R_{coil}$  = 400 to 700 m $\Omega;$   $L_{coil}$  = 2 to 6 mH unless otherwise specified  $^{(a)}$  .

Table 5. Electrical characteristics

	Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
	.,	I Pada calka wa alawa	$I_C = 7 A^{(1)}$	340	370	400	V
	V <sub>cl</sub>	High voltage clamp	I <sub>C</sub> = 2 A; Switching off from 7 A	300		400	V
			I <sub>C</sub> = 6 A; V <sub>CC</sub> = 14 V; V <sub>IN</sub> = 4 V			2	V
	V <sub>cg(sat)</sub>	Power stage saturation voltage	$I_C = 7 \text{ A}; V_{CC} = 14 \text{ V};$ $V_{IN} = 4 \text{ V}^{(2)}$				V
	1	Power-off supply current	V <sub>IN</sub> = 0.4 V; V <sub>CC</sub> = 14 V			20	mA
	I <sub>CC(off)</sub>	rower-on supply current	$V_{IN} = 0.4 \text{ V}; V_{CC} = 24 \text{ V}^{(3)}$ (4)	All		80	mA
			$V_{IN} = 4 \text{ V}; V_{CC} < 14 \text{ V}; I_{C} = 4 \text{ A}$	00,		200	mA
	I <sub>CC(on)</sub>	Power-on supply current	$V_{IN} = 4 \text{ V}; V_{CC} = 24 \text{ V};$ $I_{C} = 4 \text{ A}^{(3)} (4)$			300	mA
	I <sub>cl</sub>	Collector current limit	$V_{ N} = 4 \text{ V}; 10 \text{ V} < V_{CC} < 19 \text{ V}^{(5)}$	8.8		11.1	Α
	V <sub>INH</sub>	High level input voltage	202	4			V
	V <sub>INL</sub>	Low level input voltage				8.0	V
	V <sub>IN(hyst)</sub>	Hysteresis input voltage		0.4			V
	I <sub>INH</sub>	High level input current	$V_{IN} = 4 V$	10		150	μΑ
	I <sub>INL</sub>	Low level inplit current	$V_{IN} = 0.8 V$	0		30	μΑ
	V <sub>diagH</sub>	High ਿ਼ve' diagnostic output vɔl'ag ੩	$R_{EXT}$ = 22 K $\Omega$ ; $C_{EXT}$ = 1 nF <sup>(7)</sup>	3.5		5.5	V
	V <sub>≓'agL</sub>	Low level diagnostic output voltage	$R_{EXT}$ = 22 K $\Omega$ ; $C_{EXT}$ = 1 nF <sup>(7)</sup>			0.5	V
76			$T_j$ = -40 °C; 10 V < $V_{CC}$ < 19 V	5.45		6.8	Α
Obsole			$T_j = 25 ^{\circ}\text{C};  10  \text{V} < \text{V}_{\text{CC}} < 19  \text{V}$	5.55		6.35	Α
002	I <sub>C(diag)</sub>	Threshold level collector	$T_j = 125 ^{\circ}\text{C};  10  \text{V} < \text{V}_{CC} < 19  \text{V}$	5.5		6.35	Α
	'C(diag)	current <sup>(6)(8)</sup> see <i>Figure 7</i>	$T_j = -40  ^{\circ}\text{C};  V_{CC} = 7  \text{V}$	5.9		6.6	Α
			$T_j = 25 ^{\circ}\text{C};  V_{CC} = 7 ^{\circ}\text{V}$	5.7		6.3	Α
			$T_j = 125 ^{\circ}\text{C};  V_{CC} = 7 ^{\circ}\text{V}$	5.5		6.3	Α
	I <sub>diag</sub>	High level flag output current	$I_C > I_{C(diag)}^{(6)}$	0.5			mA
	I <sub>diag(leak)</sub>	Leakage current on flag output	V <sub>IN</sub> = low			10	μΑ
	V <sub>f</sub>	Diode forward voltage	I <sub>f</sub> = 10 A			3.5	V
	E <sub>s/b</sub>	Single pulse avalanche energy		300			mJ

a. Only functionality is guaranteed with 6 V <  $V_{CC}$  < 10 V and  $V_{CC}$  > 24 V and not parameter values.

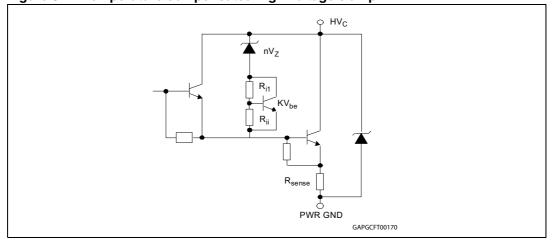
**577** 

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
T <sub>j</sub>	Thermal output current control	IN = ON <sup>(9)</sup>	150			°C
t <sub>d(on)</sub>	Turn-on delay time of output current	See <sup>(10)</sup>		1		μs
t <sub>d(off)</sub>	Turn-off delay time of output current	See <sup>(11)</sup>	7		60	μs

Table 5. Electrical characteristics (continued)

- In the high voltage clamping structure of this device a temperature compensation has been implemented. The circuit schematic is shown in *Figure 3*. The KVbe cell takes care of the temperature compensation. The whole electrical characteristic of the new circuit is shown in *Figure 4*. Up to V<sub>CE</sub> = nV<sub>Z</sub> no current flows into the collector (just the leakage current of the power stage); for nV<sub>Z</sub> < V<sub>CE</sub> < V<sub>CI</sub> a current begins to flow across the resistances of the KVbe compensation circuit (typical slope ≅ 20 KΩ) as soon as the V<sub>CI</sub> reached the dinamic resistance drop to ~4 Ω to protect the device against overvoltage (See *Figure 5*).
- 2. The saturation voltage of the Power stage includes the drop on the sensing resistor.
- 3. Considering the different ways of operation of the device (with or without spark, etc...) there are some short periods of time in which the output terminal (HV<sub>C</sub>) is pulled below ground by a negative current due to leakage inductances and stray capacitances of the ignition coil. With VIPower device: i. no corrective action is taken, these negative currents can cause parasitic glitches on the diagnostic curput. To kill this potential problem, a circuit that avoids the possibility for the HV<sub>C</sub> to be pulled under ground, by sending the required negative current from the battery is implemented in the VB125ASHTh. E. For this reason there are some short periods in which a current exceeding 220 mA flows in the V<sub>C</sub> pin.
- 4. A zener protection of 16 V (typical) is placed on the supply pin ( $V_{CC}$ ) of the chip to protect the internal circuitry. For this reason, when the battery voltage exceeds that voltage, the current flowing into  $V_{CC}$  pin can be greater than the maximum current specified at  $V_{CC} = 14$  V (both in power on and power off conditions): it will be limited by an internal resistor.
- 5. The primary coil current value I<sub>cl</sub> must be measured 1 ms after desaturation of the power stage.
- 6. These limits apply with regard to the minimum a tery voltage and resistive drop on the coil and cables that permit to reach the limitation or diagnostic evel
- 7. No internal pull-down.
- 8. When  $I_C$  gets over  $I_{C(diag)}$ , the Gagn astic output voltage rises to the high level and so it remains until the end of the input signal.
- 9. T<sub>jmin</sub> = 150 °C means that the behavior of the device will not be affected for junction temperature lower than 150 °C. For higher to negative, the thermal protection circuit begins its action reducing the I<sub>ct</sub> limit according with the lower dissipation. Chip temperature is a function of the R<sub>th</sub> of the whole system in which the device will be operating (See *Figure 6*).
- 10. Turn or cala, time measured from 90% of input voltage rising edge to 10% of output voltage falling edge.
- 11. Turn off delay time is defined as the time between the 90% of input pulse falling edge and the point where the  $HV_C$  reaches 200 V.

Figure 3. Temperature compensated high voltage clamp



I<sub>C</sub> [mA]

40

30

20

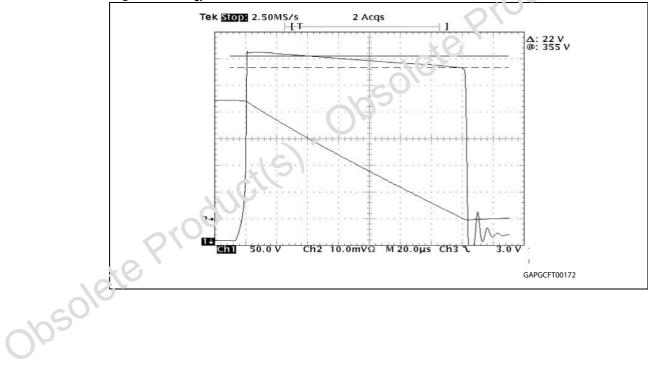
10 slope ⊠ Σ Ri

100 200 300 400 V<sub>CL</sub> V<sub>CE</sub> [V]

GAPGCFT00171

Figure 4. Electrical characteristic of the circuit shown in Figure 3





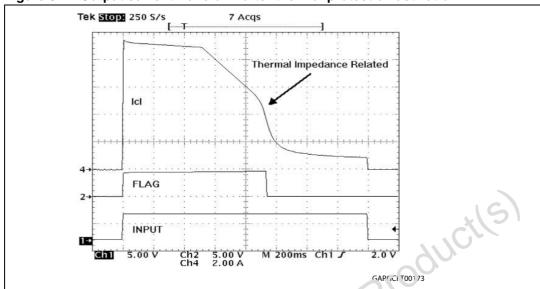
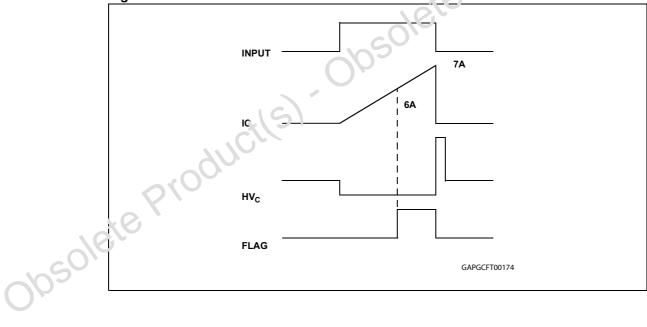


Figure 6. Output current waveform after thermal protection activation





I<sub>C(diag)</sub> (A)

7.0

6.0

5.0

4.0

-50

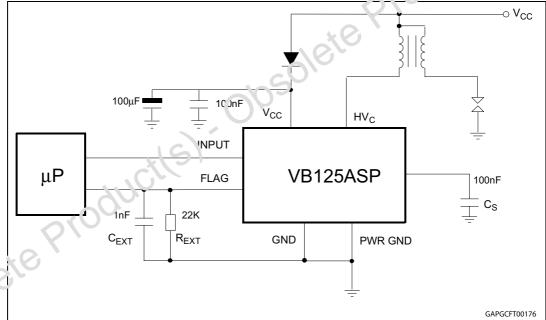
0

50

T<sub>case</sub> (°C)

Figure 8. Threshold collector current vs temperature





### 3 Package and packing information

### 3.1 ECOPACK®

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

#### 3.2 PowerSO-10 mechanical data

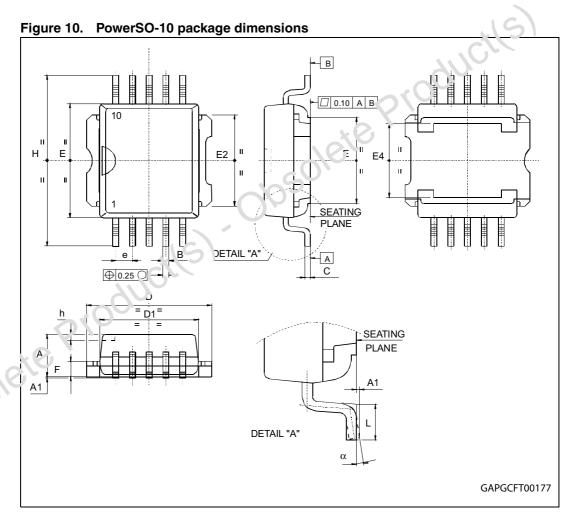


Table 6. PowerSO-10 mechanical data

Dim		mm.			inch	
Dim.	Min.	Тур	Max.	Min.	Тур.	Max.
Α	3.35		3.65	0.132		0.144
A <sup>(1)</sup>	3.4		3.6	0.134		0.142
A1	0.00		0.10	0.000		0.004
В	0.40		0.60	0.016		0.024
B <sup>(1)</sup>	0.37		0.53	0.014		0.021
С	0.35		0.55	0.013		0.022
C <sup>(1)</sup>	0.23		0.32	0.009		0.0126
D	9.40		9.60	0.370	(C)	0.378
D1	7.40		7.60	0.291	70,	0.300
E	9.30		9.50	0.366	2-	0.374
E2	7.20		7.60	0.28		0.299
E2 <sup>(1)</sup>	7.30		7.50	3.287		0.295
E4	5.90		6.10	0.232		0.240
E4 <sup>(1)</sup>	5.90		5.50	0.232		0.248
е		1.27	76		0.050	
F	1.25		1.35	0.049		0.053
F <sup>(1)</sup>	1.20	.(5)	1.40	0.047		0.055
Н	13.80		14.40	0.543		0.567
H <sup>(1)</sup>	16.გ5		14.35	0.545		0.565
h	100	0.50	_		0.002	
7	1.20		1.80	0.047	_	0.070
(-)	0.80		1.10	0.031		0.043
α	0°		8°	0°		8°
α <sup>(1)</sup>	2°		8°	2°		8°

<sup>1.</sup> Muar only POA P013P.

### 3.3 PowerSO-10 packing information

Figure 11. PowerSO-10 suggested PAD layout

Figure 12. PowerSO-10 tube shipment (no suffix)

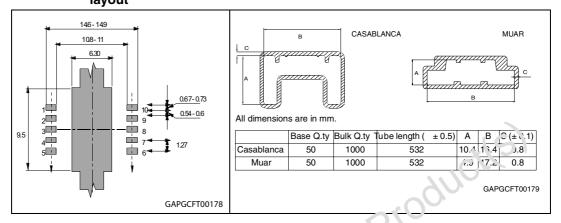
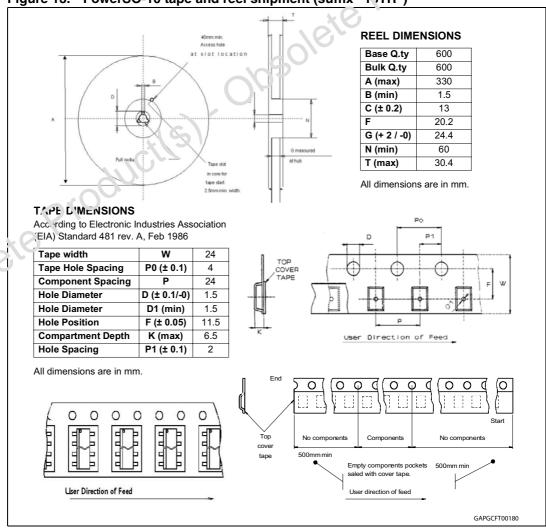


Figure 13. PowerSO-10 tape and reel shipment (suffix ") (TR")



Revision history VB125ASPTR-E

# 4 Revision history

Table 7. Document revision history

Date	Revision	Changes
13-May-2011	1	Initial release.



#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidia, 'ec' ('ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and sen ice's described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and solvices described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property Liq. is s granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a marranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained in a single single.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE ANCION SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNE'SE FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN VIRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARHANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCT'S OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PF OP ENTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of S. p. or ucts with provisions different from the statements and/or technical features set forth in this document shall immediately void any war and granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liabi. f. C.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2011 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

577

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

STMicroelectronics: VB125ASPTR-E